2SK4088LS

N-Channel Power MOSFET 650V, 11A, 0.85Ω, TO-220F-3FS



http://onsemi.com

Features

- ON-resistance RDS(on)= 0.65Ω (typ.)
- · 10V drive

• Input capacitance Ciss=1000pF (typ.)

Specifications

Absolute Maximum Ratings at Ta=25°C

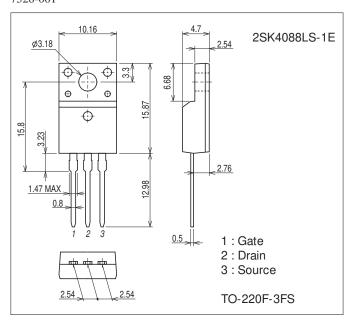
Parameter	Symbol	Conditions	Ratings	Unit
Drain to Source Voltage	V _{DSS}		650	V
Gate to Source Voltage	VGSS		±30	V
Drain Current (DC)	I _{Dc} *1	Limited only by maximum temperature Tch=150°C	11	Α
	I _{Dpack} *2	Tc=25°C (Our ideal heat dissipation condition)*3	7.5	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	40	Α
Allowable Power Dissipation	Do		2.0	W
	PD	Tc=25°C (Our ideal heat dissipation condition)*3	37	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *4	EAS		65	mJ
Avalanche Current *5	IAV		11	Α

- Note:*1 Shows chip capability
 - *2 Package limited
 - *3 Our condition is radiation from backside.
 - The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.
 - *4 VDD=50V, L=1mH, IAV=11A (Fig.1)
 - *5 L≤1mH, single pulse

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit : mm (typ) 7528-001

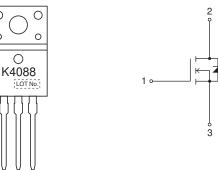


Ordering & Package Information

	Device	Package	Shipping	memo
2SK40)88LS-1E	TO-220F-3FS, SC-67	50pcs./tube	Pb-Free

Marking

Electrical Connection

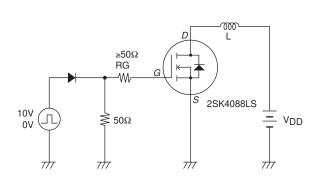


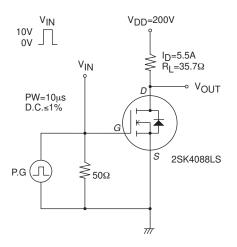
Electrical Characteristics at Ta=25°C

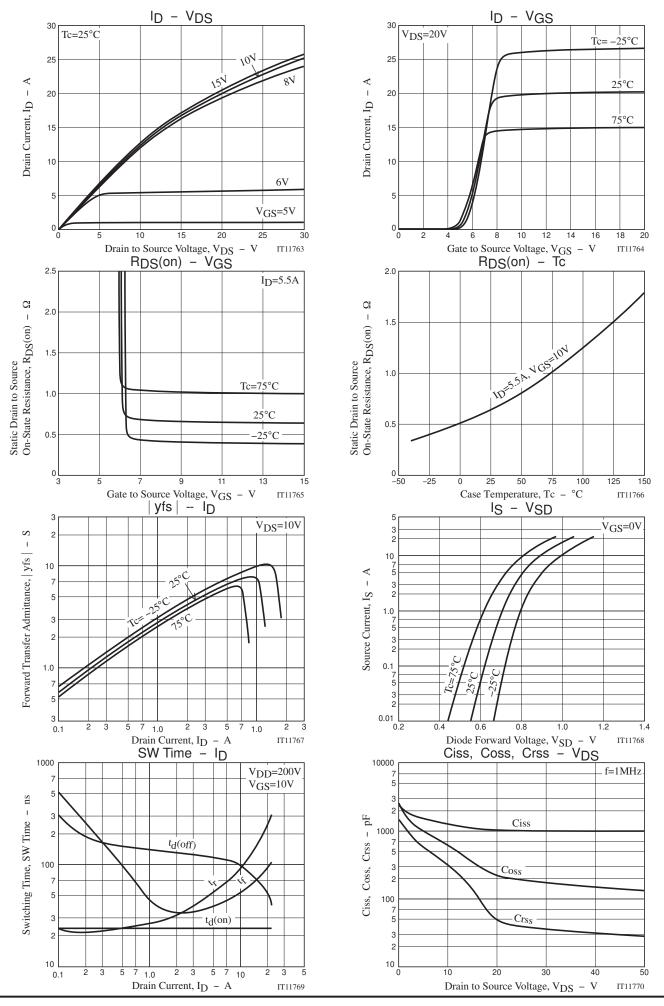
Parameter	Symbol	Conditions	Ratings			Unit
Farameter	Symbol	Symbol Conditions		typ	max	Onit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=10mA, VGS=0V	650			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =520V, V _{GS} =0V			100	μΑ
Gate to Source Leakage Current	IGSS	V _{GS} =±30V, V _{DS} =0V			±100	nA
Cutoff Voltage	V _{GS} (off)	V _{DS} =10V, I _D =1mA	3		5	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =5.5A	3.3	6.5		S
Static Drain to Source On-State Resistance	R _{DS} (on)	I _D =5.5A, V _G S=10V		0.65	0.85	Ω
Input Capacitance	Ciss			1000		pF
Output Capacitance	Coss	V _{DS} =30V, f=1MHz		172		pF
Reverse Transfer Capacitance	Crss			36		pF
Turn-ON Delay Time	td(on)			24		ns
Rise Time	t _r	One are selfied Took Circuit		58		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		117		ns
Fall Time	tf			40		ns
Total Gate Charge	Qg			37.6		nC
Gate to Source Charge	Qgs	V _{DS} =200V, V _{GS} =10V, I _D =11A		6.8		nC
Gate to Drain "Miller" Charge	Qgd			17.6		nC
Diode Forward Voltage	V _{SD}	I _S =11A, V _{GS} =0V		0.9	1.2	V

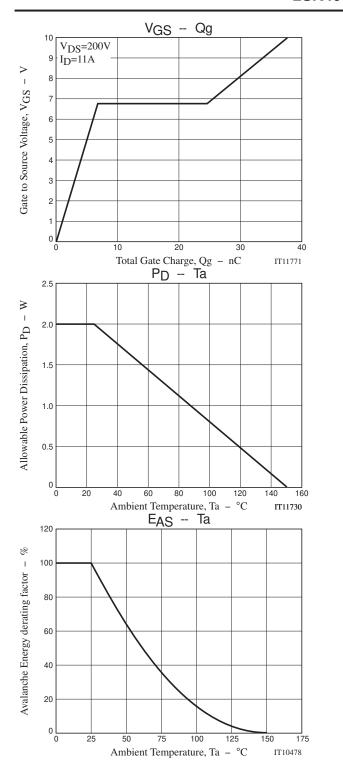
Fig.1 Unclamped Inductive Switching Test Circuit

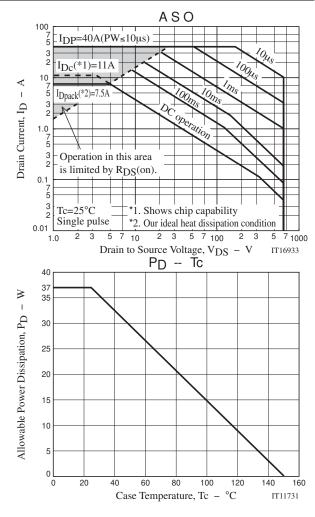
Fig.2 Switching Time Test Circuit









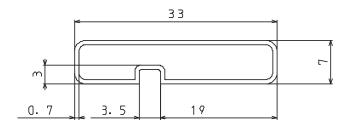


Magazine Specification

2SK4088LS-1E

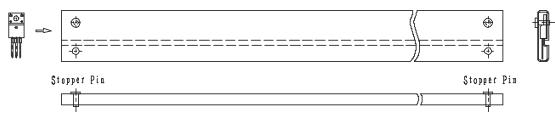
1. Packing Format

Package Name	Name Magazine Name		Maximum Number of devices contained (pcs)		Packing format		
1 4 4 4 5 4 1 4 4 4 4	Idag as the Hams	I	Inner box	Outer box	Inner BOX	Outer BOX	
TO-220F-3F\$	TO-220F	50	1, 000	4,000	SPD-0V0001 20 magazines contained Dimensions:mm (external) 568×150×55	SPT-081029 4 inner boxes contained Dinensions:mm (external) 590×225×178	



Tolerance=±0.3mm
Thickness=0.7±0,2mm
Length =532.5±2mm
Material =PVC (Antistatic treatment)

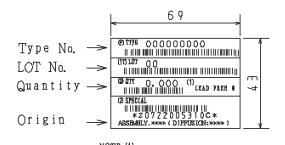
3. Storage method to magazine

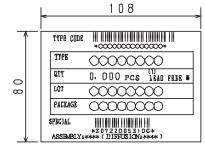


4. Inner box label (unit:mm)

5. Outer box label (unit:mm)

It is a label at the time of factory shipments. The form of a label may change in physical distribution process.



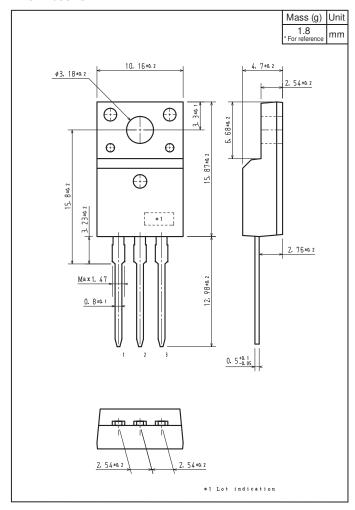


The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

Label		JEITA Phase
LEAD FREE	3	JEITA Phase 3A

Outline Drawing

2SK4088LS-1E



Note on usage: Since the 2SK4088LS is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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